



الجامعة الإسلامية العالمية ماليزيا

**INTERNATIONAL ISLAMIC UNIVERSITY MALAYSIA
END OF SEMESTER EXAMINATION
SEMESTER I, 2011/2012 SESSION
KULLIYYAH OF ENGINEERING**

Programme : ENGINEERING Level of Study : UG 2
Time : 2:30 pm-5:30 pm Date : 08/01/2012
Duration : 3 Hrs
Course Code : ECE 2133 Section(s) : 1
Course Title : **Electronic Circuits**

This Question Paper consists of Six (6) Printed Pages (Including cover and a blank page) with Five (5) Questions.

INSTRUCTION(S) TO CANDIDATES

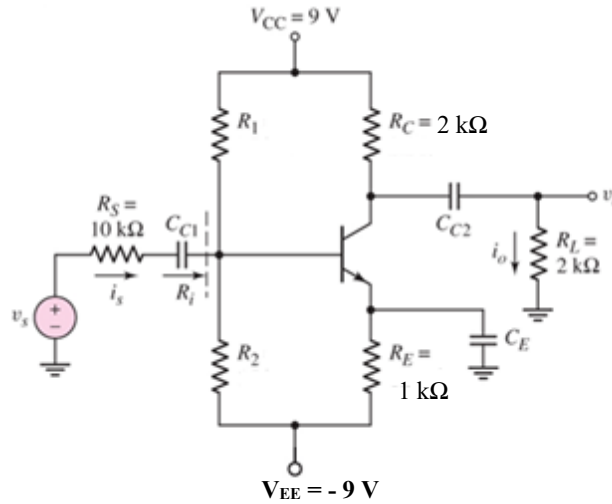
DO NOT OPEN UNTIL YOU ARE ASKED TO DO SO

- A total mark of this examination is **100**.
- This examination is worth **50%** of the total assessment.
- Answer **ALL FIVE (5)** questions.

Any form of cheating or attempt to cheat is a serious offence which may lead to dismissal.

Q.1 [20 marks]

- (a) For the transistor parameters for the circuit is shown in **Fig. 1(a)** are $\beta=100$ and $V_A=100$. (i) Design the circuit such that it is biased stable and the $V_{CEQ}=1.0$ V and $V_{BE}=0.7$ V. (ii) Find the small-signal hybrid- π parameters r_π , g_m and r_o and draw the small signal equivalent circuit for the midband frequency range. **(10 marks)**



$$g_m = \frac{I_{CQ}}{V_T}$$

$$r_\pi = \frac{\beta V_T}{I_{CQ}}$$

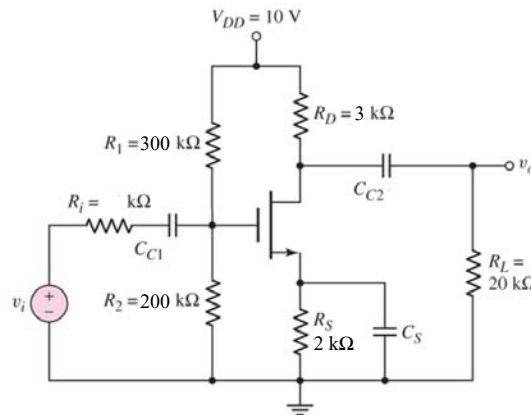
$$g_m r_\pi = \beta$$

$$r_o = \frac{V_A}{I_{CQ}}$$

$$V_T = 26 \text{ mV}$$

Fig. 1(a)

- (b) The FET circuit is shown in **Fig. 1(b)**, the transistor parameters are: $K_n = 1 \text{ mA/V}^2$, $V_{TN}=2\text{V}$ and $\lambda = 0.01 \text{ V}^{-1}$. Find (i) the quiescent current I_{DQ} . (ii) Find the small-signal hybrid- π parameters g_m and r_o and draw the small signal equivalent circuit for the midband frequency range. All capacitors are $10 \mu\text{F}$. **(10 marks)**



$$g_m = \sqrt{2K_n I_{DQ}}$$

$$r_o = \frac{1}{\lambda I_{DQ}}$$

Fig. 1(b)

Q.2 [20 marks]

- (a) The common emitter transistor amplifier is shown in **Fig. 2(a)** and the transistor has small signal hybrid- π parameters, $r_{\pi} = 4\text{k}\Omega$, $g_m = 20\text{mA/V}$ and $r_o = \infty$. Find (i) the midband frequency voltage gain, $A_v = v_o/v_s$ and (ii) the input resistance R_i of the amplifier. **(10 marks)**

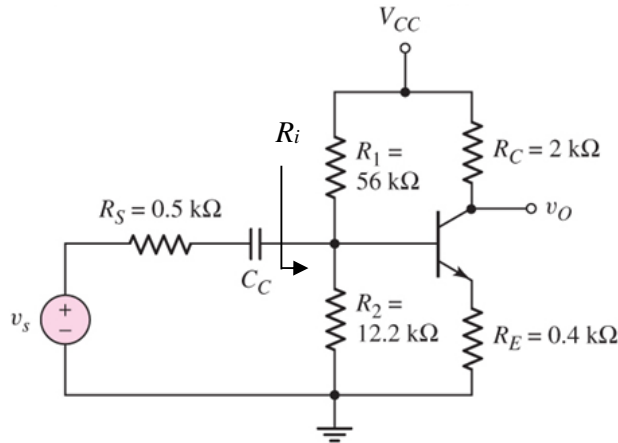


Fig. 2(a)

- (b) The Darlington pair transistor is shown in **Fig. 2(b)**. Prove that the current of the Darlington pair amplifier is given by $A_i = \beta_1\beta_2$. [Symbols have their usual meanings] **(6 marks)**

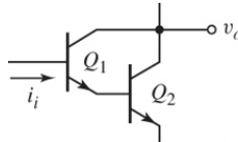


Fig. 2(b)

- (c) Draw the Bode plot (magnitude and phase) of the following transfer functions. **(4 marks)**

(i) $H(s) = \frac{10}{(s+1000)}$

(ii) $H(s) = \frac{10000s}{(s+100)}$

Q.3 [20 marks]

(a) The common collector transistor amplifier is shown in **Fig. 3(a)** and the transistor has small signal hybrid- π parameters, $r_\pi = 4 \text{ k}\Omega$, $g_m = 20 \text{ mA/V}$ and $r_o = 100 \text{ k}\Omega$. The value of coupling capacitance is infinity. Find:

- (i) the voltage gain, $A_v = v_o/v_s$ of the amplifier. **(2 marks)**
- (ii) the current gain, $A_i = i_o/i_s$ the amplifier. **(3 marks)**
- (iii) the input resistance, R_{is} of the amplifier. **(2 marks)**
- (iv) the output resistance, R_o of the amplifier. **(3 marks)**

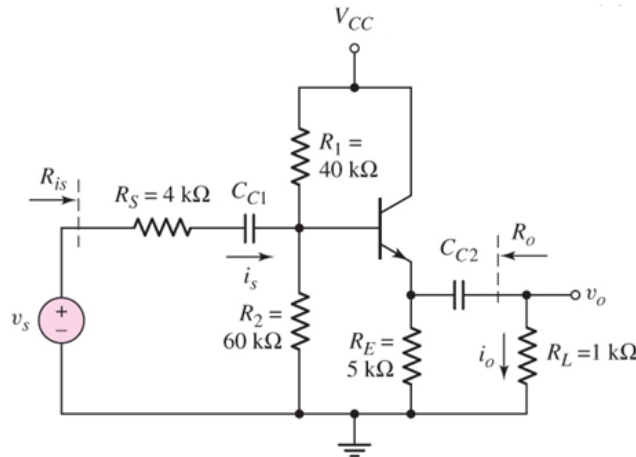


Fig. 3(a)

(b) Draw the typical frequency response of an amplifier and discuss the behavior of the response. **(3 marks)**

(c) Determine the lower 3 dB frequency (f_L) of the common emitter transistor with DC blocking capacitor as shown in **Fig. 3(c)**. The transistor parameters are: $V_{BE} = 0.7$ (on), $\beta = 120$, and $V_A = \infty$. [Other information can be found in this question]

(7 marks)

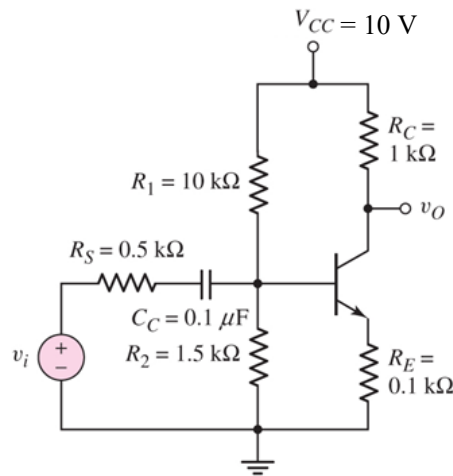


Fig 3(c)

Q.4 [20 marks]

- (a) Determine the Miller capacitance and the upper 3 dB frequency (f_H) with and without Miller capacitance of the common emitter circuit shown in **Fig. 4(a)**. The transistor parameters are: $r_\pi = 4 \text{ k}\Omega$, $g_m = 40 \text{ mA/V}$ and $r_o = \infty$, $C_\pi = 35 \text{ pF}$, and $C_\mu = 4 \text{ pF}$.

(10 marks)

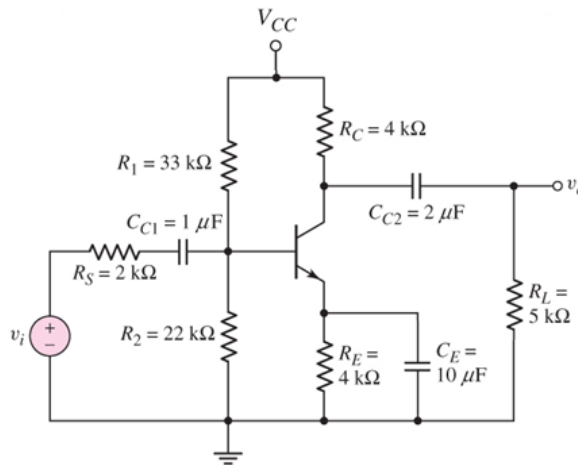


Fig. 4(a)

- (b) Design a Wildlar current source as shown in **Fig. 4(b)** such that $I_{REF} = 1.5 \text{ mA}$ and $I_o = 15 \mu\text{A}$. Assume that $V^+ = +5 \text{ V}$, $V^- = -5 \text{ V}$, and $V_{BE1} = 0.7 \text{ V}$. [Collector current is approximately given by $I_C = I_s e^{V_{BE}/V_T}$, where I_s is the reverse saturation current and V_T is the thermal voltage, $V_T = 26 \text{ mV}$]

(10 marks)

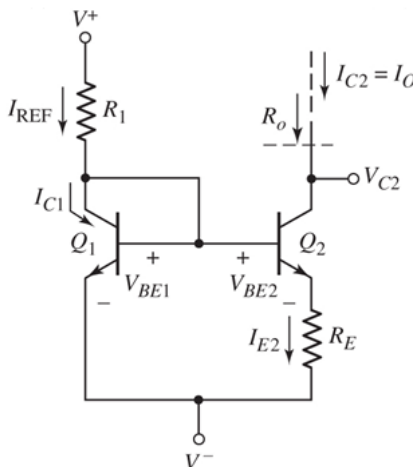


Fig. 4(b)

Q.5 [20 marks]

- (a) Design a MOSFET current source as shown in **Fig. 5(a)** such that $I_{REF} = 0.5\text{mA}$ and $I_o = 0.1\text{mA}$. The bias voltage $V^+ = +5\text{ V}$ and $V^- = -5\text{ V}$. The transistors are available with parameters $k'_n = 40\mu\text{A}/\text{V}^2$, $V_{TN} = 1\text{ V}$ and $\lambda = 0$. **(7 marks)**

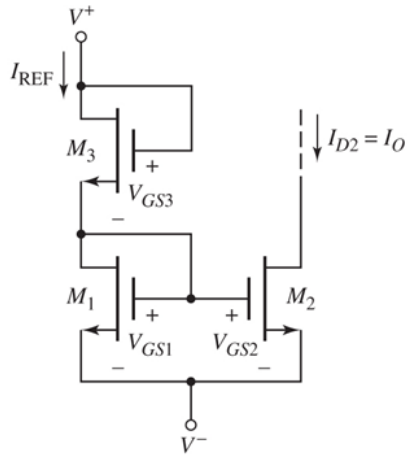


Fig. 5(a)

- (b) What is a feedback system? Write down the advantages and disadvantages of a negative feedback amplifier. **(3 marks)**
- (c) Draw the block diagram of a basic feedback amplifier and derive the closed-loop transfer function as $A_f = \frac{A}{1 + \beta A}$. [The symbols have their usual meanings] **(4 marks)**
- (d) The series-shunt feedback topology is shown in **Fig. 5(d)**. Draw the equivalent circuit configuration of an ideal series-shunt feedback amplifier. Derive the closed-loop voltage gain, A_f , input resistance with feedback, R_{if} and output resistance with feedback, R_{of} . **(6 marks)**

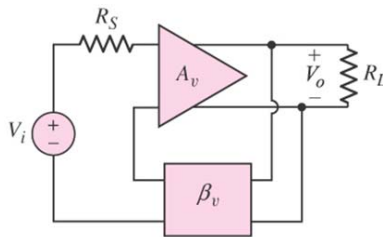


Fig. 5(d)